Vincotech

10-EZ12B2A040MS-LQ17L73T
datasheet

flowBOOST E1 SiC **1200 V / 40 mΩ**

Topology features

- Dual Booster
- Integrated DC capacitor
- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Target applications

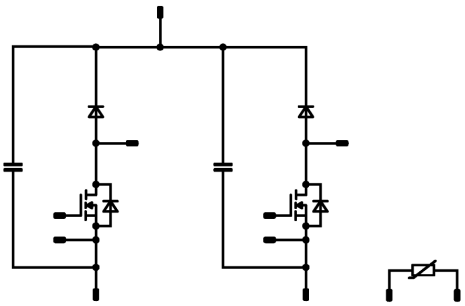
- Charging Stations
- Energy Storage Systems
- Power Supply
- Solar Inverters
- UPS
- Welding & Cutting

Types

- 10-EZ12B2A040MS-LQ17L73T

flow E1 12 mm housing

Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Boost Switch					
Drain-source voltage	V_{DSS}			1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$	T_s = 80 °C	43	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}		120	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	73	W
Gate-source voltage	V_{GSS}	static		0 / 18	V
		dynamic		-5 / 22	V
Maximum Junction Temperature	T_{jmax}			175	°C
Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	27	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 25 °C	142	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	73	W
Maximum junction temperature	T_{jmax}			175	°C
Boost Sw. Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	45	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	270	A
Surge current capability	I^2t			370	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	53	W
Maximum junction temperature	T_{jmax}			150	°C
Capacitor (DC)					
Maximum DC voltage	V_{MAX}			1500	V
Operation Temperature	T_{op}			-55 ... 125	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			9,02	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		18		30	25 125 150		37,9 36,8 39,2	55,2[1]	mΩ
Gate-source threshold voltage	$V_{GS(th)}$				0,003	25	3,6	4,6	5,6	V
Gate to Source Leakage Current	I_{GSS}		22	0		25			200	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25			100	µA
Internal gate resistance	r_g							3		Ω
Gate charge	Q_g		0/18		30	25		185		nC
Short-circuit input capacitance	C_{iss}		0	10	0	25		4000		pF
Short-circuit output capacitance	C_{oss}							1300		
Reverse transfer capacitance	C_{rss}							110		
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,3		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/18	600	32	25 125 150		42,39 32,24 30,72		ns
Rise time	t_r					25 125 150		28,08 19,47 18,56		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		96,82 122,35 129,28		ns
Fall time	t_f					25 125 150		7,78 8,1 8,02		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,058 µC Q_{rFWD}=0,079 µC Q_{rFWD}=0,083 µC				25 125 150		0,833 0,59 0,565		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,242 0,237 0,242		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Diode										
Static										
Forward voltage	V_F				20	25 125 150		1,51 2,03 2,13	1,8(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25		60	500	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,3		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=1384 A/µs di/dt=1731 A/µs di/dt=2704 A/µs	0/18	600	32	25 125 150		7,36 10,31 10,79		A
Reverse recovery time	t_{rr}					25 125 150		13,31 13,31 13,18		ns
Recovered charge	Q_r					25 125 150		0,058 0,079 0,083		µC
Reverse recovered energy	E_{rec}					25 125 150		$2,511x10^{-3}$ $4,147x10^{-3}$ $4,525x10^{-3}$		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		1991,57 3178,45 3190,63		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Sw. Protection Diode										
Static										
Forward voltage	V_F				28	25 125		1,1 1,04	1,5[1]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,31		K/W
Capacitor (DC)										
Static										
Capacitance	C	DC bias voltage = 0 V				25		6,8		nF
Tolerance							-10		10	%
Dissipation factor		f = 1 kHz				25		0,15		%
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 499 Ω				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3380		K
Vincotech Thermistor Reference									V	

[1] Value at chip level

[2] Only valid with pre-applied Vincotech thermal interface material.

Boost Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics

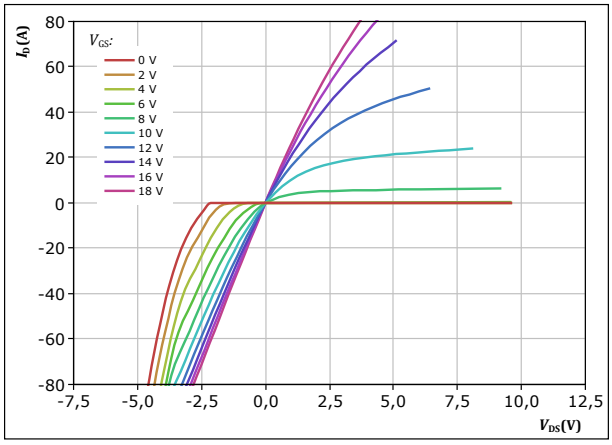
$I_D = f(V_{DS})$

t_p =	250	µs		
V_{GS} =	18	V	T_j:	25 °C
				125 °C
				150 °C

figure 2. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$



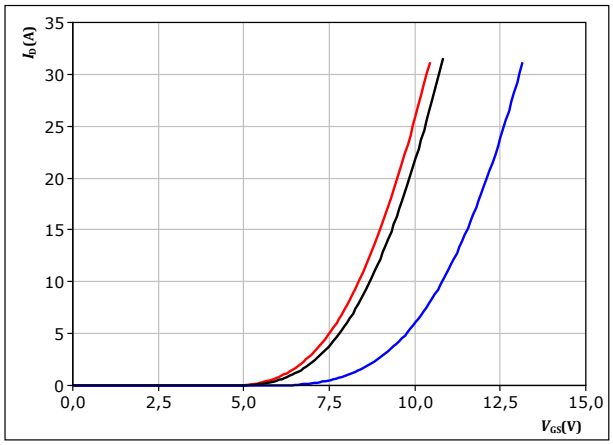
t_p =	250	µs
T_j =	150	°C

V_{GS} from 0 V to 18 V in steps of 2 V

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$

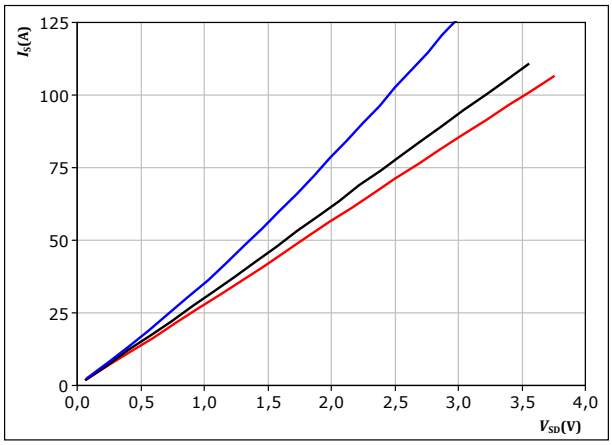


t_p =	250	µs		
V_{DS} =	10	V	T_j:	25 °C
				125 °C
				150 °C

figure 4. **MOSFET**

Typical reverse drain current characteristics

$I_{SD} = f(V_{SD})$



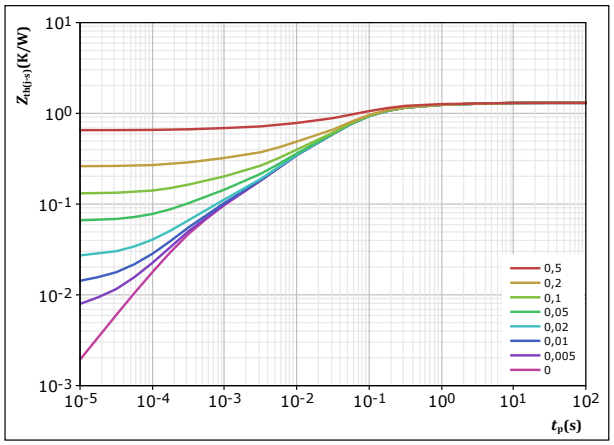
t_p =	250	µs		
V_{GS} =	18	V	T_j:	25 °C
				125 °C
				150 °C

Boost Switch Characteristics

figure 5. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D =$ t_p / T

$R_{th(j-s)} =$ 1,305 K/W

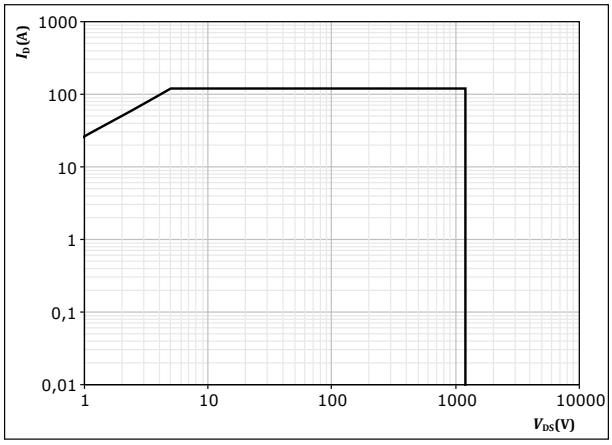
MOSFET thermal model values

R (K/W)	τ (s)
8,10E-02	2,89E+00
2,17E-01	2,87E-01
7,39E-01	5,99E-02
2,09E-01	6,28E-03
5,87E-02	3,95E-04

figure 6. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



$D =$ single pulse

$T_s =$ 80 °C

$V_{GS} =$ 18 V

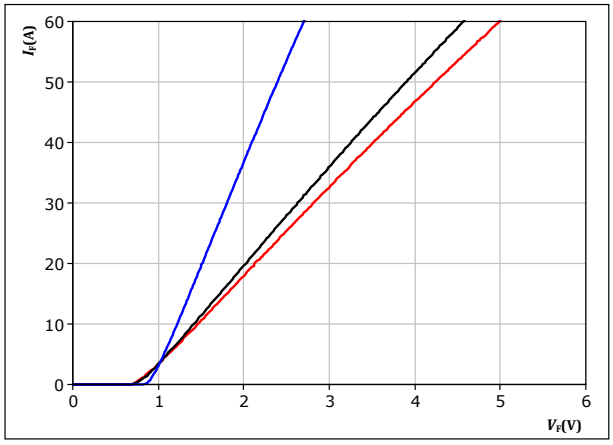
$T_j =$ T_{jmax}

Boost Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



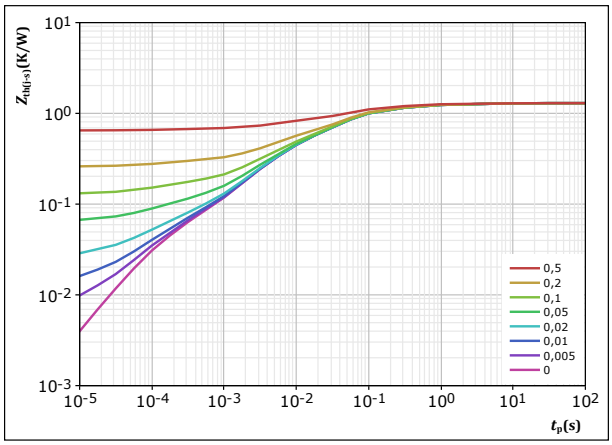
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,296 K/W

FWD thermal model values

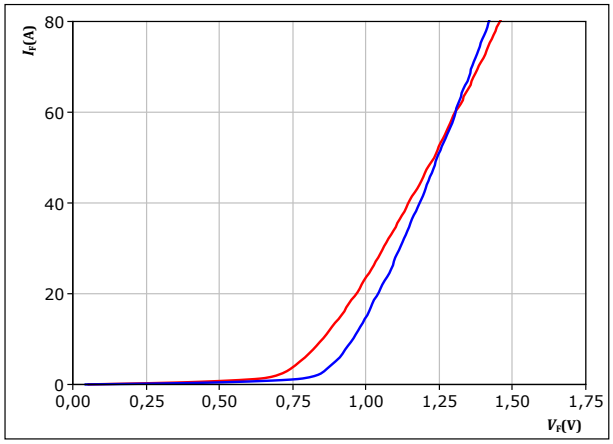
R (K/W)	τ (s)
6,22E-02	4,27E+00
2,36E-01	2,99E-01
6,69E-01	4,31E-02
2,88E-01	4,14E-03
4,04E-02	1,25E-04

Boost Sw. Protection Diode Characteristics

figure 9. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



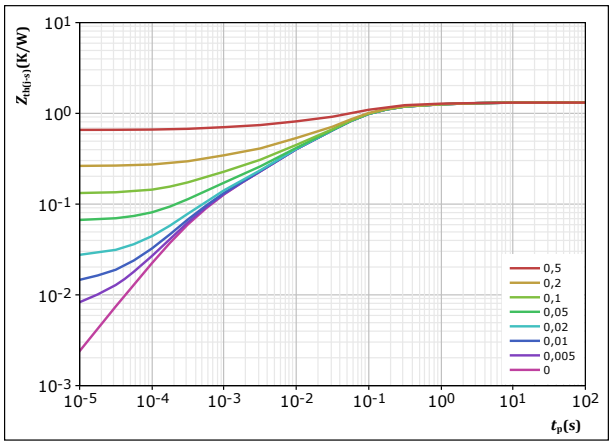
t_p = 250 µs

T_j: 25 °C, 125 °C

figure 10. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,314 K/W

Rectifier thermal model values

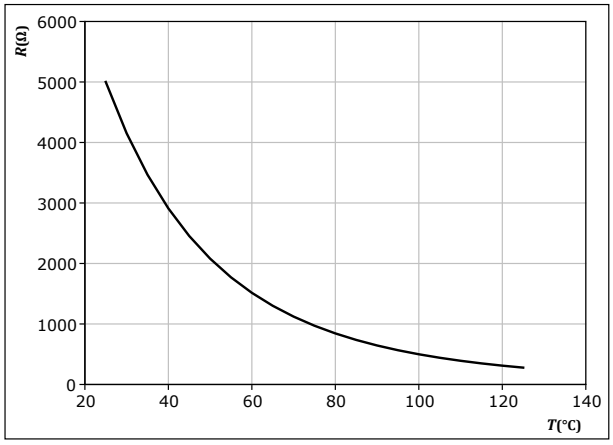
R (K/W)	τ (s)
8,85E-02	1,99E+00
2,65E-01	1,87E-01
6,64E-01	4,96E-02
2,12E-01	5,03E-03
8,48E-02	4,58E-04

Thermistor Characteristics

figure 11. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

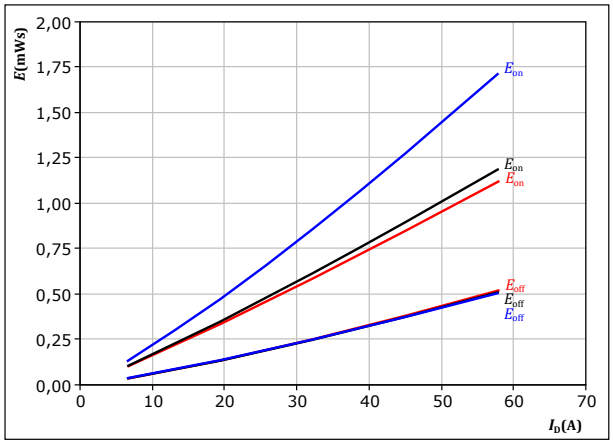


Boost Switching Characteristics

figure 12. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



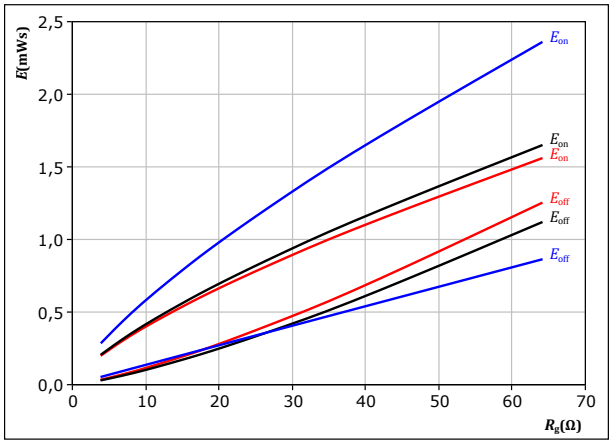
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	0/18	V		125 °C
R_{gon} =	16	Ω		150 °C
R_{goff} =	16	Ω		

figure 13. **MOSFET**

Typical switching energy losses as a function of MOSFET turn on gate resistor

$E = f(R_g)$



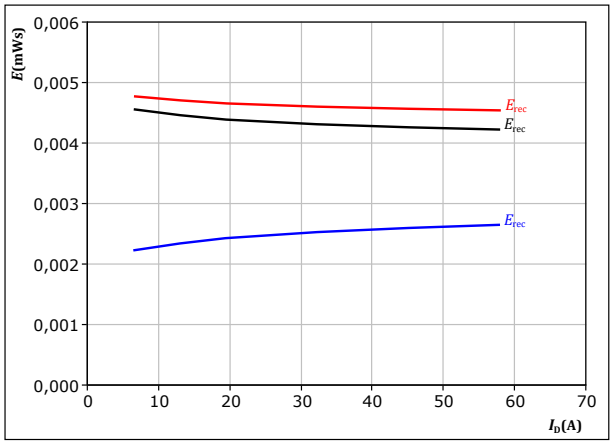
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	0/18	V		125 °C
I_D =	32	A		150 °C

figure 14. **FWD**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



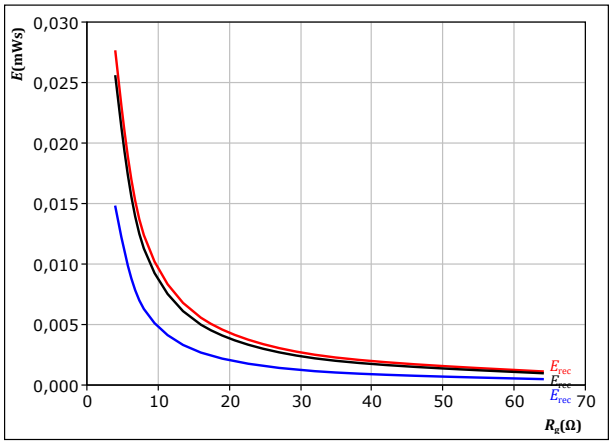
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	0/18	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 15. **FWD**

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

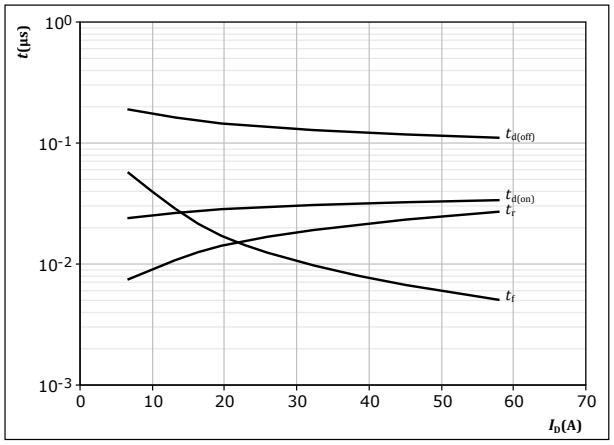
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	0/18	V		125 °C
I_D =	32	A		150 °C

Boost Switching Characteristics

figure 16. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



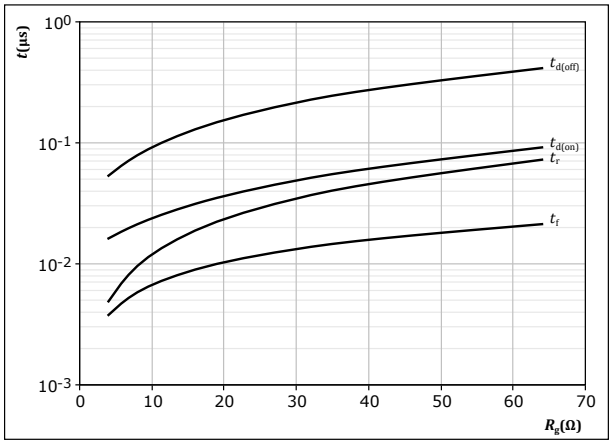
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	0/18	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 17. **MOSFET**

Typical switching times as a function of MOSFET turn on gate resistor

$t = f(R_g)$



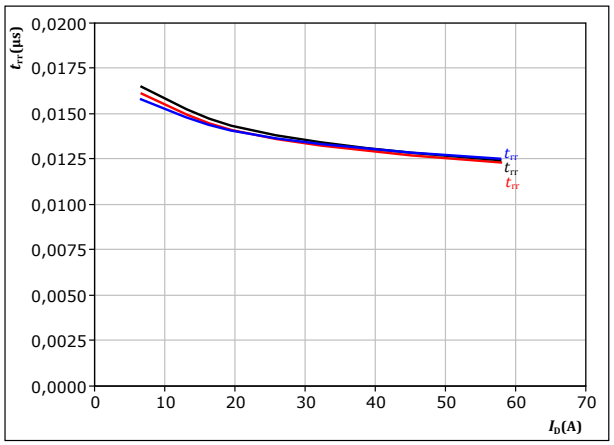
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	0/18	V
I_D =	32	A

figure 18. **FWD**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



At

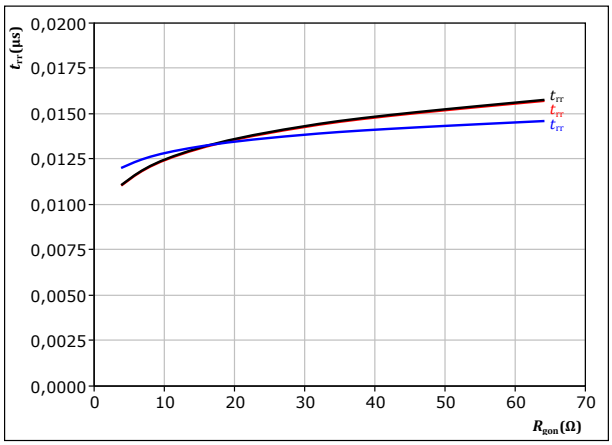
V_{DS} =	600	V
V_{GS} =	0/18	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 19. **FWD**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

$t_{rr} = f(R_{gon})$



At

V_{DS} =	600	V
V_{GS} =	0/18	V
I_D =	32	A

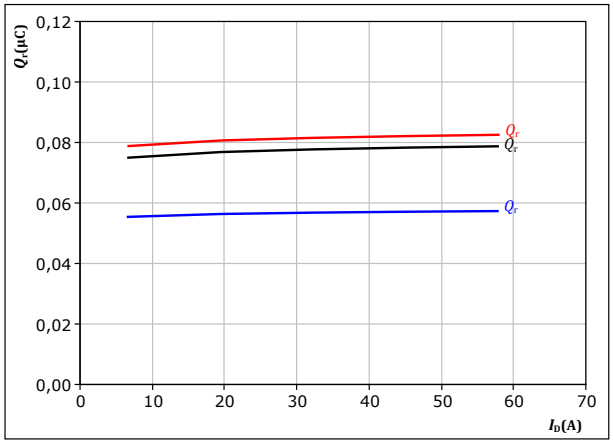
T_j: 25 °C, 125 °C, 150 °C

Boost Switching Characteristics

figure 20. **FWD**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

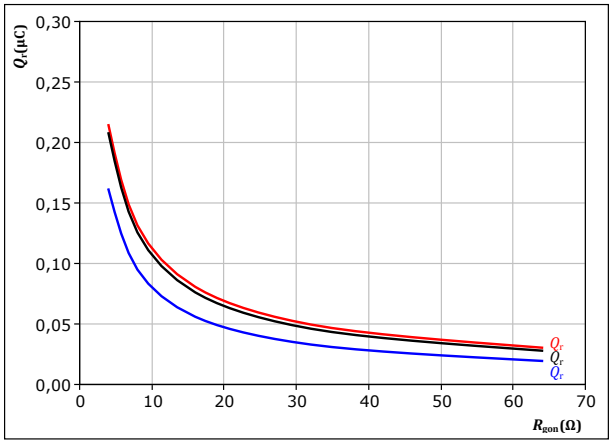


At					
	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	R_{gon} =	16	Ω		125 °C
					150 °C

figure 21. **FWD**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$

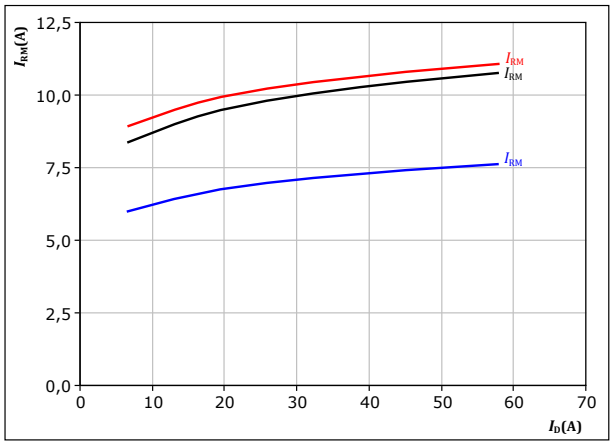


At					
	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	I_D =	32	A		125 °C
					150 °C

figure 22. **FWD**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

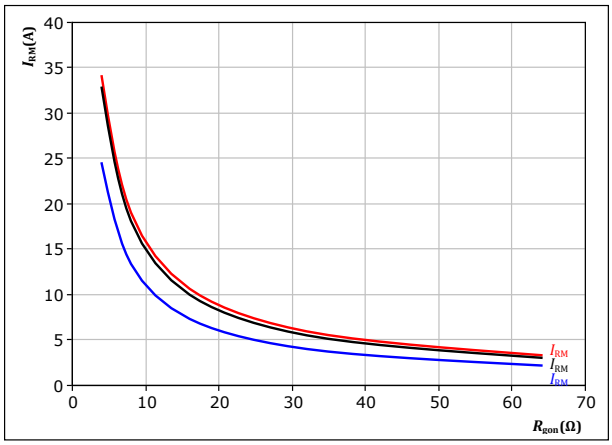


At					
	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	R_{gon} =	16	Ω		125 °C
					150 °C

figure 23. **FWD**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



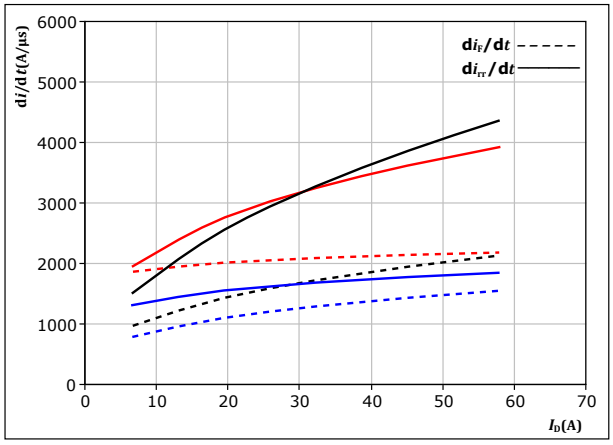
At					
	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	I_D =	32	A		125 °C
					150 °C

Boost Switching Characteristics

figure 24. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

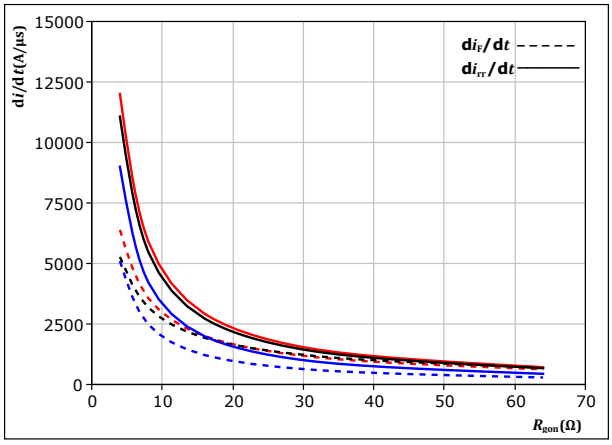


At	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	R_{gon} =	16	Ω		125 °C
					150 °C

figure 25. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

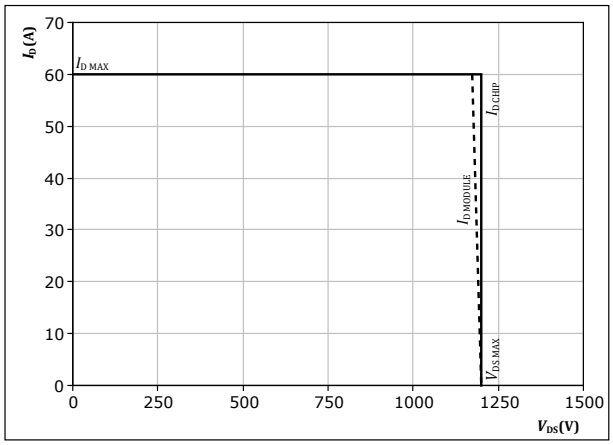


At	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	I_D =	32	A		125 °C
					150 °C

figure 26. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Boost Switching Definitions

figure 27. MOSFET

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

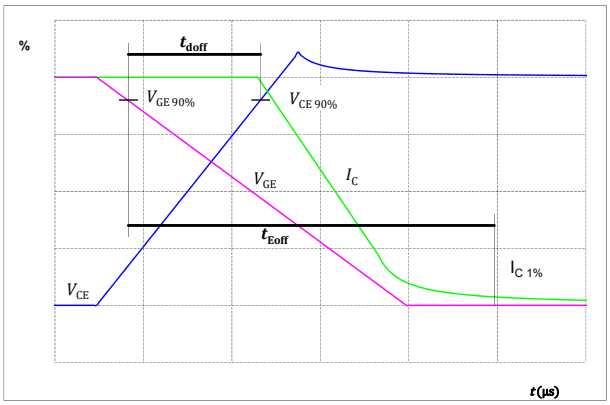


figure 28. MOSFET

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

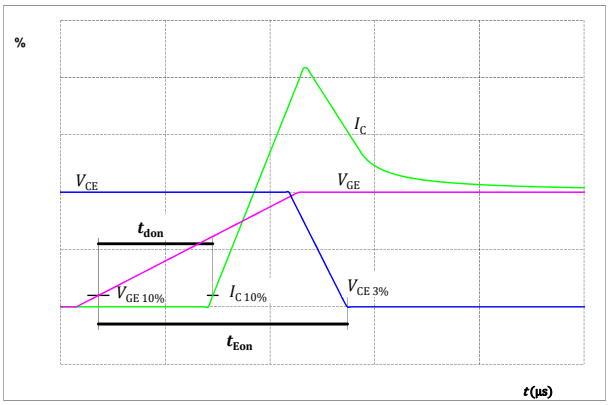


figure 29. MOSFET

Turn-off Switching Waveforms & definition of t_f

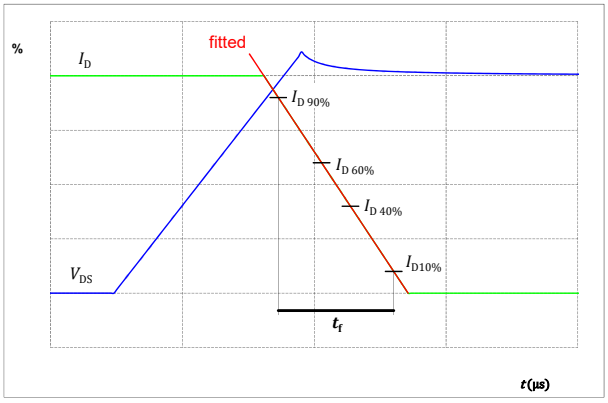
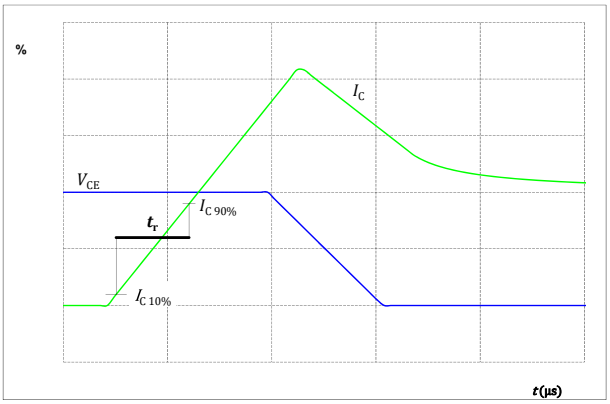


figure 30. MOSFET

Turn-on Switching Waveforms & definition of t_r



Boost Switching Definitions

figure 31. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

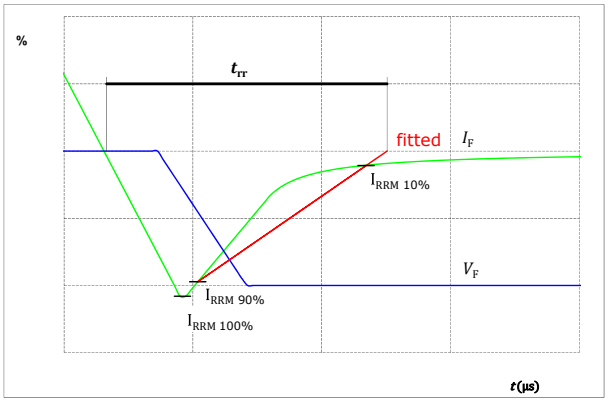


figure 32. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

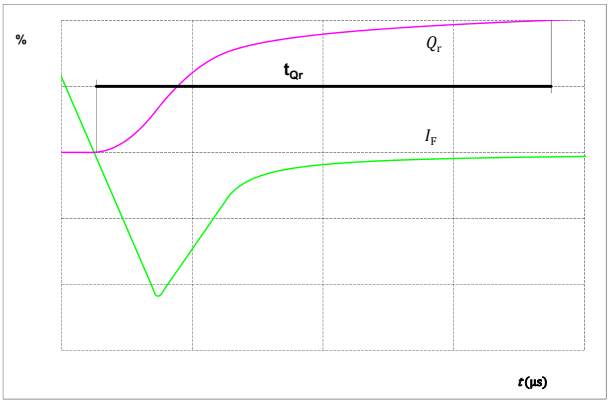
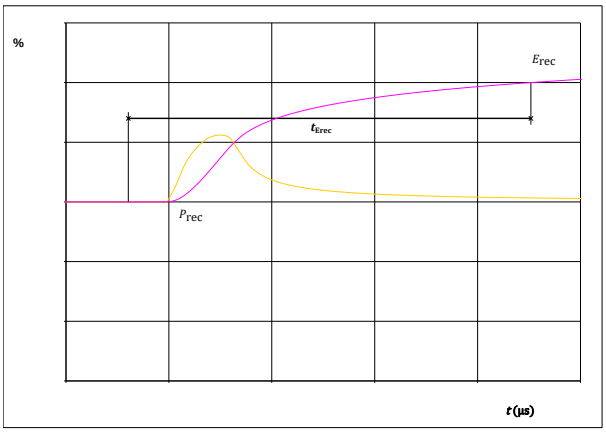


figure 33. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Ordering Code

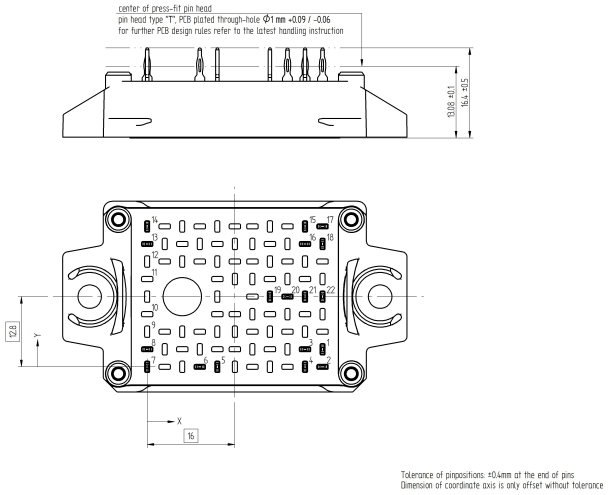
Version	Ordering Code
Without thermal paste	10-EZ12B2A040MS-LQ17L73T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EZ12B2A040MS-LQ17L73T-/7/

Marking

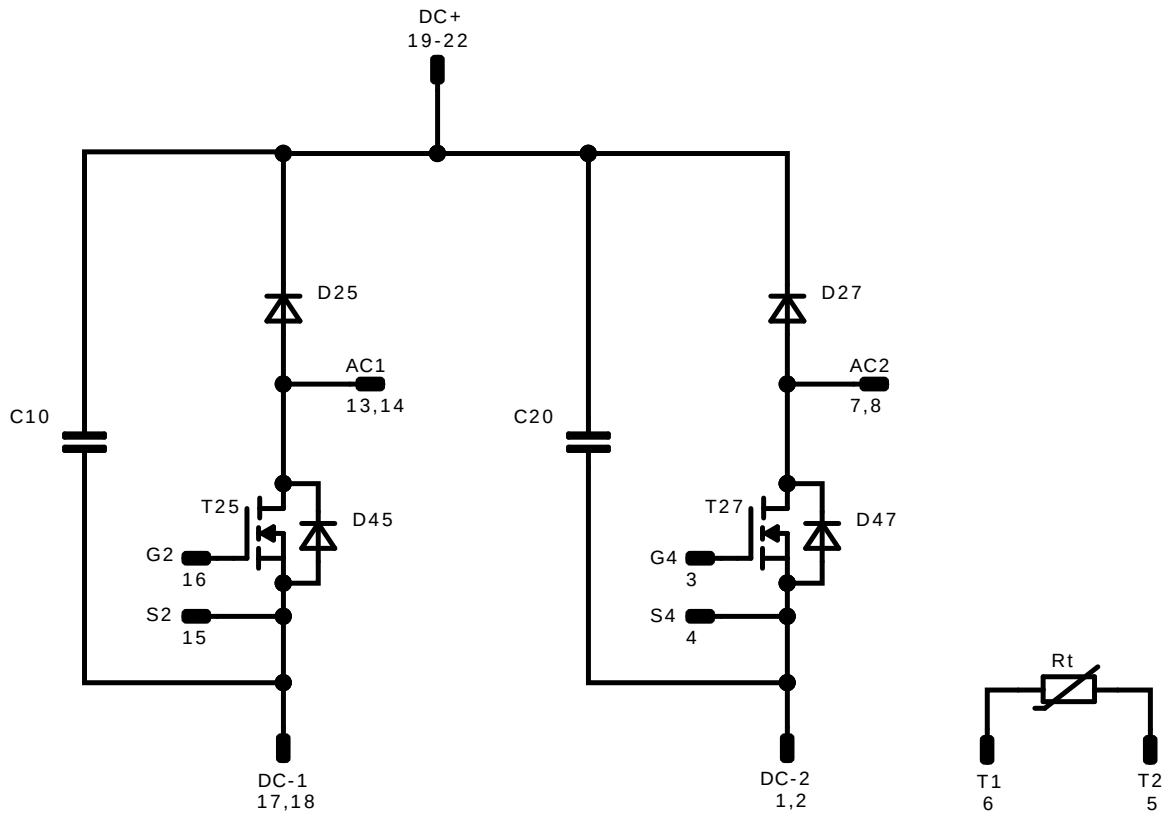
		Name		Date code	UL & VIN	Lot	Serial
Text		NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix		**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]			
Pin	X	Y	Function
1	32	3,2	DC-2
2	32	0	DC-2
3	28,8	3,2	G4
4	28,8	0	S4
5	12,8	0	T2
6	9,6	0	T1
7	0	0	AC2
8	0	3,2	AC2
9	not assembled		
10	not assembled		
11	not assembled		
12	not assembled		
13	0	22,4	AC1
14	0	25,6	AC1
15	28,8	25,6	G2
16	28,8	22,4	S2
17	32	25,6	DC-1
18	32	22,4	DC-1
19	22,4	12,8	DC+
20	25,6	12,8	DC+
21	28,8	12,8	DC+
22	32	12,8	DC+



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T25, T27	MOSFET	1200 V	40 mΩ	Boost Switch	
D25, D27	FWD	1200 V	20 A	Boost Diode	
D45, D47	Rectifier	1600 V	28 A	Boost Sw. Protection Diode	
C25, C27	Capacitor	1500 V		Capacitor (DC)	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E1 packages see vincotech.com website.

Package data
Package data for *flow* E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-EZ12B2A040MS-LQ17L73T-D1-14	30 Jul. 2024	Initial Release	
10-EZ12B2A040MS-LQ17L73T-D2-14	16 Apr. 2026	Correct Vgs of the Boost Switch Correct Outline drawing and Pintable	